

# HiPerFET™

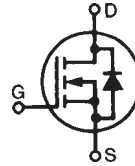
## Power MOSFETs

### Q2-Class

## IXFK30N100Q2

## IXFX30N100Q2

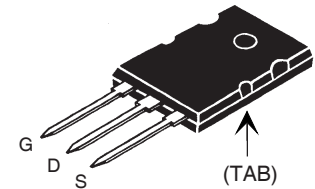
N-Channel Enhancement Mode  
 Avalanche Rated, High dv/dt, Low Q<sub>g</sub>  
 Low intrinsic R<sub>g</sub>, low t<sub>rr</sub>



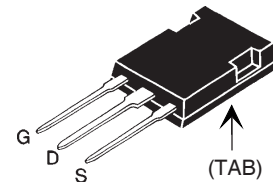
**V<sub>DSS</sub>** = 1000V  
**I<sub>D25</sub>** = 30A  
**R<sub>DS(on)</sub>** ≤ 400mΩ  
**t<sub>rr</sub>** ≤ 300ns

Symbol	Test Conditions	Maximum Ratings	
<b>V<sub>DSS</sub></b>	T <sub>J</sub> = 25°C to 150°C	1000	V
<b>V<sub>DGR</sub></b>	T <sub>J</sub> = 25°C to 150°C, R <sub>GS</sub> = 1MΩ	1000	V
<b>V<sub>GSS</sub></b>	Continuous	± 30	V
<b>V<sub>GSM</sub></b>	Transient	± 40	V
<b>I<sub>D25</sub></b>	T <sub>C</sub> = 25°C	30	A
<b>I<sub>DM</sub></b>	T <sub>C</sub> = 25°C, pulse width limited by T <sub>JM</sub>	120	A
<b>I<sub>A</sub></b>	T <sub>C</sub> = 25°C	30	A
<b>E<sub>AS</sub></b>	T <sub>C</sub> = 25°C	4	J
<b>dv/dt</b>	I <sub>S</sub> ≤ I <sub>DM</sub> , V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 150°C	20	V/ns
<b>P<sub>D</sub></b>	T <sub>C</sub> = 25°C	735	W
<b>T<sub>J</sub></b>		-55 ... +150	°C
<b>T<sub>JM</sub></b>		150	°C
<b>T<sub>stg</sub></b>		-55 ... +150	°C
<b>T<sub>L</sub></b>	1.6mm (0.062 in.) from case for 10s	300	°C
<b>T<sub>SOLD</sub></b>	Plastic body for 10s	260	°C
<b>M<sub>d</sub></b>	Mounting torque (IXFK)	1.13/10	Nm/lb.in.
<b>F<sub>C</sub></b>	Mounting force (IXFX)	20..120 /4.5..27	N/lb.
<b>Weight</b>	TO-264	10	g
	PLUS247	6	g

TO-264 (IXFK)



PLUS247 (IXFX)



G = Gate      D = Drain  
 S = Source    TAB = Drain

### Features

- Double metal process for low gate resistance
- International standard packages
- Epoxy meet UL 94 V-0, flammability classification
- Avalanche energy and current rated
- Fast intrinsic Rectifier

### Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C unless otherwise specified)		
		Min.	Typ.	Max.
<b>BV<sub>DSS</sub></b>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 3mA	1000		V
<b>V<sub>GS(th)</sub></b>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 8mA	3.0		5.5 V
<b>I<sub>GSS</sub></b>	V <sub>GS</sub> = ± 30V, V <sub>DS</sub> = 0V			± 200 nA
<b>I<sub>DSS</sub></b>	V <sub>DS</sub> = V <sub>DSS</sub> V <sub>GS</sub> = 0V			50 μA 2 mA
<b>R<sub>DS(on)</sub></b>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> , Note 1			400 mΩ

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}, I_D = 0.5 \cdot I_{D25}$ , Note 1	20	30	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		9400	pF
$C_{oss}$			766	pF
$C_{rss}$			153	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)		22	ns
$t_r$			14	ns
$t_{d(off)}$			60	ns
$t_f$			10	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		186	nC
$Q_{gs}$			46	nC
$Q_{gd}$			82	nC
$R_{thJC}$			0.17	$^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ unless otherwise specified)		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			30 A
$I_{SM}$	Repetitive, pulse width limited by $T_{JM}$			120 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 25\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			300 ns
$Q_{RM}$			1	$\mu\text{C}$
$I_{RM}$			10	A

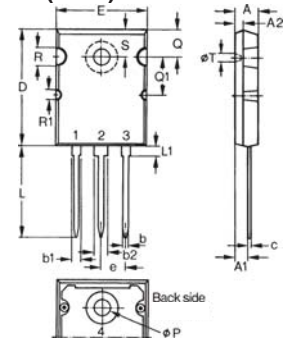
Note 1: Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

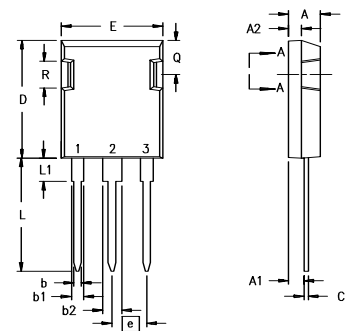
4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

### TO-264 (IXFK) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

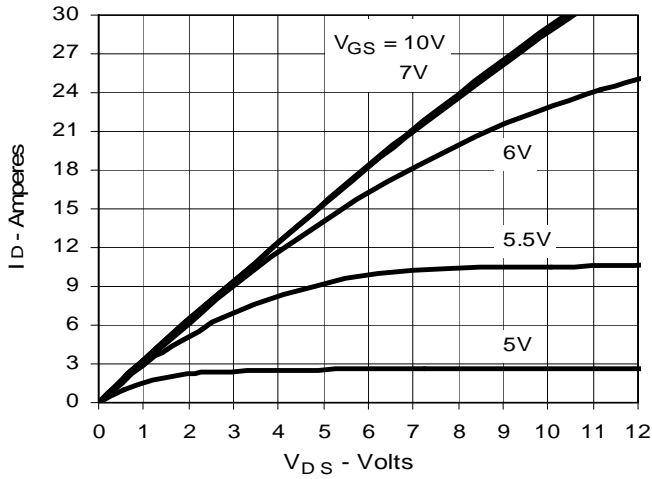
### PLUS247™ (IXFX) Outline



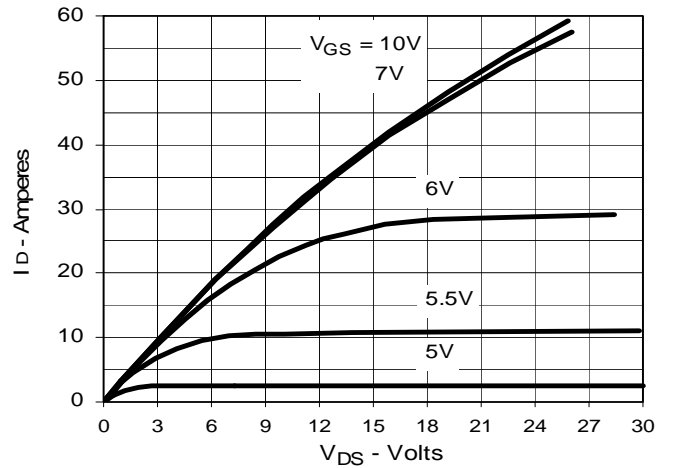
Terminals: 1 - Gate  
2 - Drain (Collector)  
3 - Source (Emitter)  
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

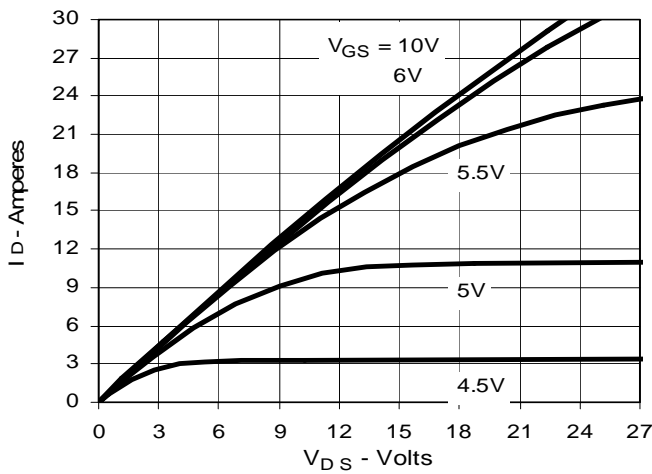
**Fig. 1. Output Characteristics**  
@ 25°C



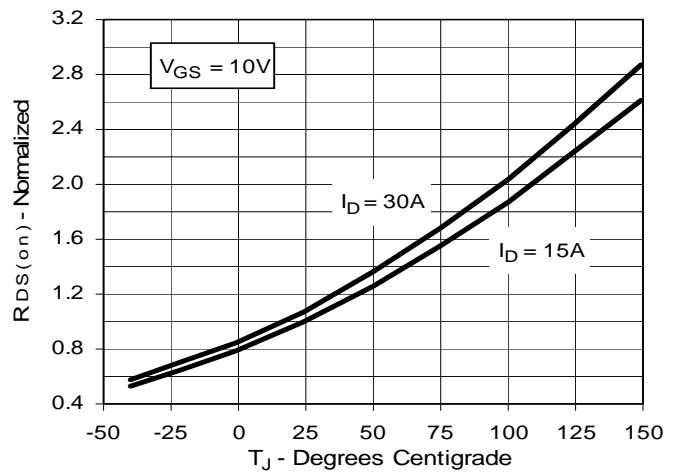
**Fig. 2. Extended Output Characteristics**  
@ 25°C



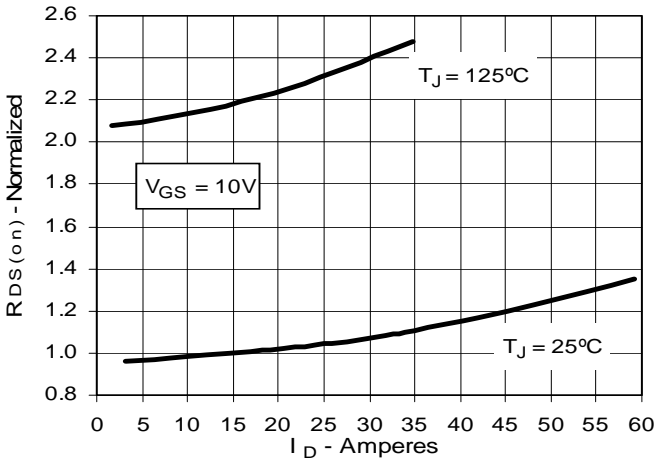
**Fig. 3. Output Characteristics**  
@ 125°C



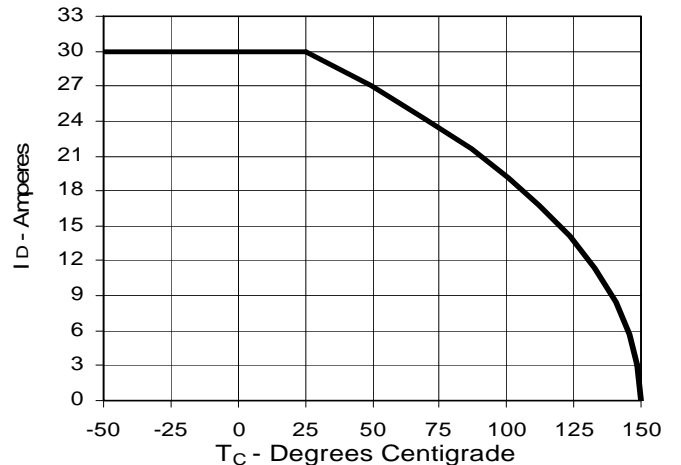
**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs. Junction Temperature**



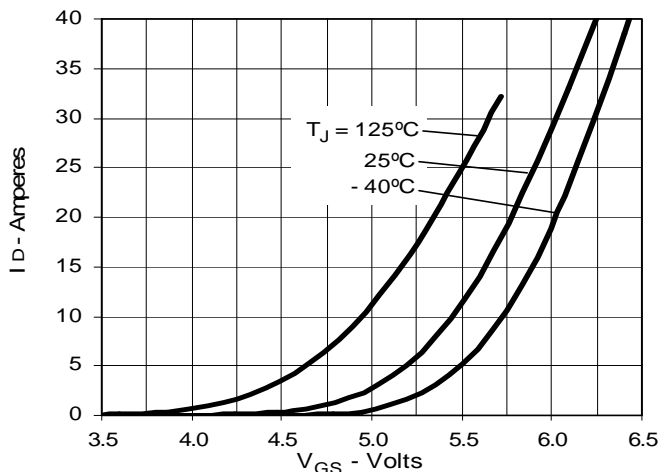
**Fig. 5.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs.  $I_D$**



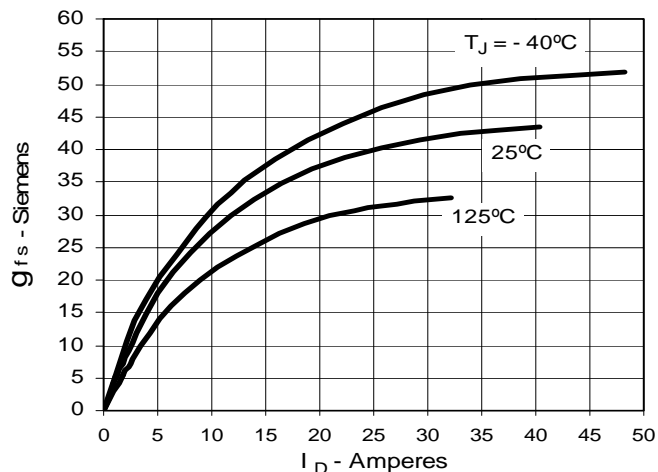
**Fig. 6. Drain Current vs. Case Temperature**



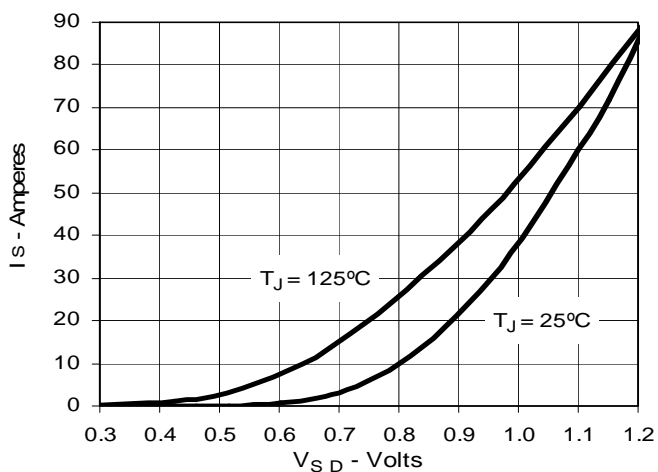
**Fig. 7. Input Admittance**



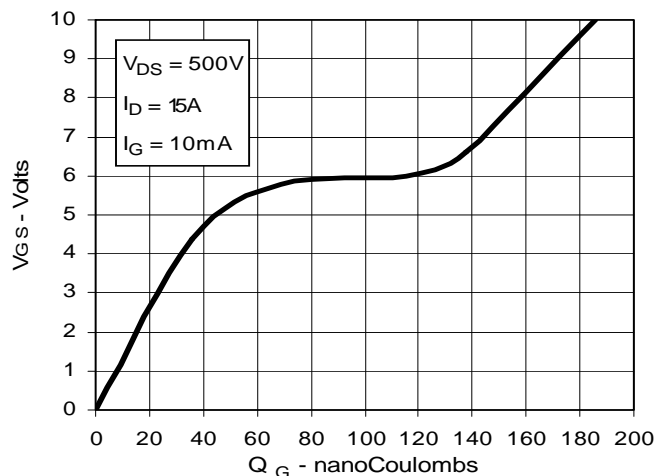
**Fig. 8. Transconductance**



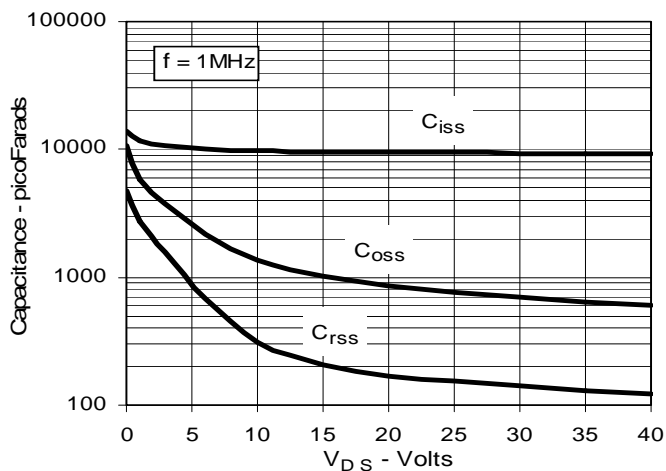
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Impedance**

